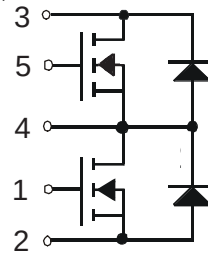


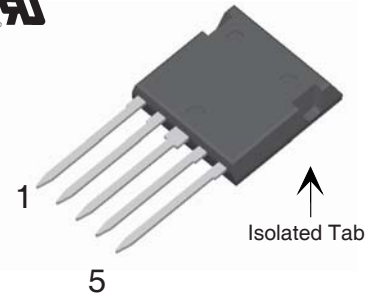
PolarHV™ HiPerFET N-Channel Power MOSFET Phase Leg Topology

FMM22-05PF



$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 13A \\ R_{DS(on)} &\leq 270m\Omega \\ t_{rr(max)} &\leq 200ns \end{aligned}$$

ISOPLUS i4-Pak™



Symbol	Test Conditions	Maximum Ratings	
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
V_{ISOLD}	50/60Hz, RMS, t = 1min, leads-to-tab	2500	~V
T_L	1.6mm (0.062 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
F_C	Mounting force	20..120 / 4.5..27	N/lb.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	13	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	55	A
I_A	$T_C = 25^\circ\text{C}$	22	A
E_{AS}	$T_C = 25^\circ\text{C}$	750	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	132	W

Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
 - UL recognized package
 - Isolated mounting surface
 - 2500V electrical isolation
- Avalanche rated
- Low Q_g
- Low Drain-to-Tab capacitance
- Low package inductance

Advantages

- Low gate drive requirement
- High power density
- Fast intrinsic rectifier
- Low drain to ground capacitance
- Fast switching

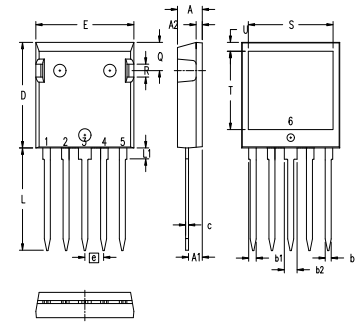
Applications

- DC and AC motor drives
- UPS, solar and wind power inverters
- Synchronous rectifiers
- Multi-phase DC to DC converters
- Industrial battery chargers
- Switching power supplies

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
C_p	Coupling capacitance between shorted pins and mounting tab in the case		40	pF
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
Weight			9	g

Symbol	Test Conditions ² (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	500		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1mA	3.0		5.0 V
I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0V			± 100 nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0V T _J = 125°C			5 μA 250 μA
R _{DS(on)}	V _{GS} = 10V, I _D = 11A, Note 1			270 mΩ
g _{fs}	V _{DS} = 20V, I _D = 11A, Note 1		20	S
C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2630	pF
C _{oss}			310	pF
C _{rss}			27	pF
t _{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 22A R _G = 10Ω (External)		22	ns
t _r			25	ns
t _{d(off)}			72	ns
t _f			21	ns
Q _{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 11A		50	nC
Q _{gs}			16	nC
Q _{gd}			18	nC
R _{thJC}				0.95 °C/W
R _{thCS}			0.15	°C/W

ISOPLUS i4-Pak™ Outline



NOTE: Bottom heatsink meets 3000 Volts AC 1 sec isolation to the other pins.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
b2	.100	.110	2.54	2.79
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Ref: IXYS CO 0077 R0

Source-Drain Diode

Symbol	Test Conditions ³	Characteristic Values		
		Min.	Typ.	Max.
I _S	V _{GS} = 0V			13 A
I _{SM}	Repetitive, pulse width limited by T _{JM}			55 A
V _{SD}	I _F = 22A, V _{GS} = 0V, Note 1			1.5 V
t _{rr}	I _F = 22A, -di/dt = 100A/μs V _R = 100V, V _{GS} = 0V	7.0	0.7	200 ns
I _{RM}				A
Q _{RM}				μC

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2 %.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated objective result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	